Thyristor Semiconductor Device - Page 1 of 2



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Inclosure Material:
Metal
Overall Length:
0.310 inches
Mounting Facility Quantity:
1
Internal Configuration:
Junction contact
Electrode Internally-electrically Connected To Case:
Anode
Mounting Method:
Threaded stud
Features Provided:
Hermetically sealed case
Overall Width Across Flats:
0.437 inches
Thread Size:
0.190 inches
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
600.0 breakover voltage, dc
Current Rating Per Characteristic:
5.00 amperes source cutoff current
Power Rating Per Characteristic:
500.0 milliwatts small-signal input power, common-collector blank
Maximum Operating Tempurature Per Measurement Point:
100.0 degrees celsius junction
Special Features:
Junction pattern arrangement: pnpn
Thread Series Designator:
Unf
Terminal Type And Quantity:
2 tab, solder lug and 1 threaded stud
Specification Data:
80131-release5221 professional/industrial association specification
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
No

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Thyristor Semiconductor Device - Page 2 of 2

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